LCE P-Channel Enhancement Mode Power MOSFET

Description

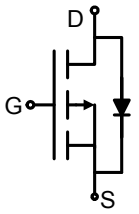
The LCE3407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

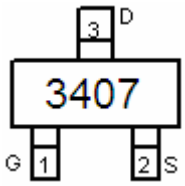
- V_{DS} = -30V,I_D = -4.1A
  $R_{DS(ON)}$ < 95mΩ @ V_{GS}=-4.5V
  $R_{DS(ON)}$ < 65mΩ @ V_{GS}=-10V
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment

SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407	LCE3407	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-4.1	A
Drain Current-Pulsed (Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V	-	-	-1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-4.1A	-	48	65	mΩ
		V_{GS}=-4.5V, I_D=-4A	-	60	95	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-4.1A	5.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C_{oss}		-	105	-	PF
Reverse Transfer Capacitance	C_{rss}		-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V,R_L=3.6Ω V_{GS}=-10V,R_{GEN}=3Ω	-	8.5	-	nS
Turn-on Rise Time	t_r		-	4.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	12.5	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-4A,V_{GS}=-10V	-	12.5	-	nC
Gate-Source Charge	Q_{gs}		-	2.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-4.1A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

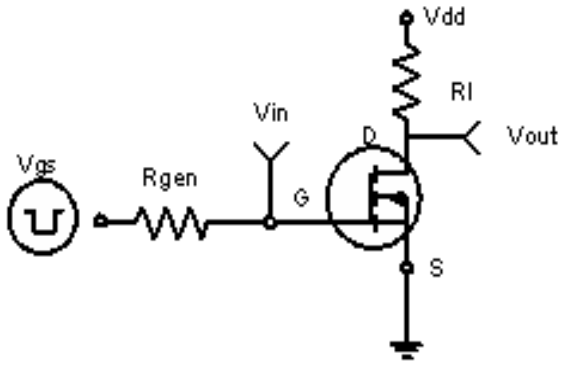


Figure 1:Switching Test Circuit

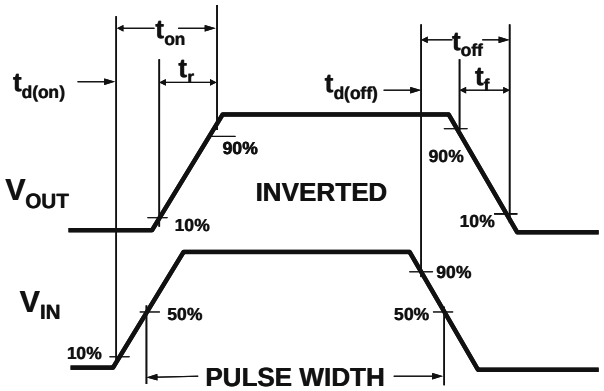


Figure 2:Switching Waveforms

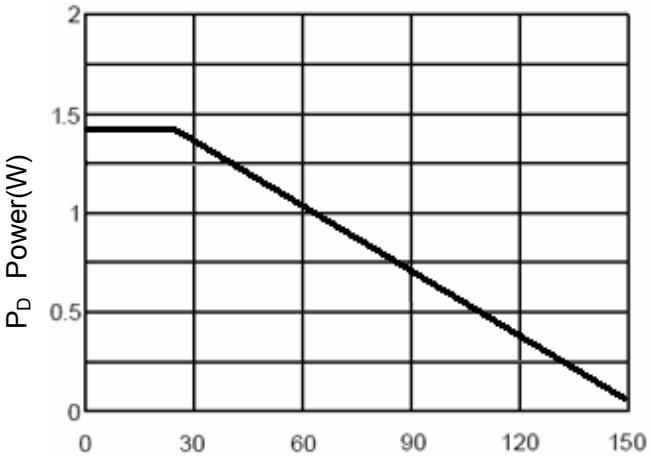


Figure 3 Power Dissipation

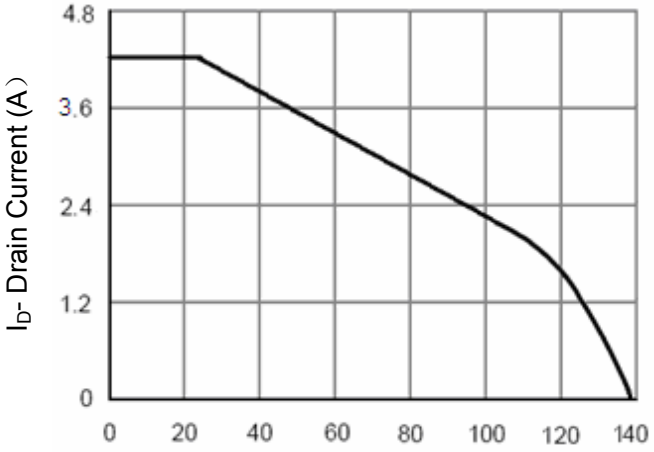


Figure 4 Drain Current

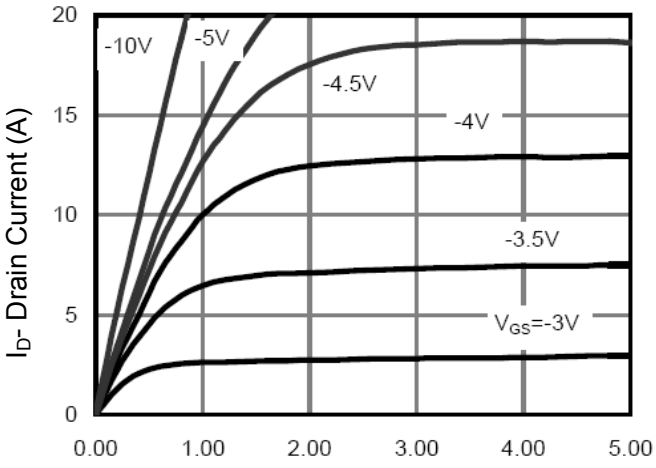


Figure 5 Output Characteristics

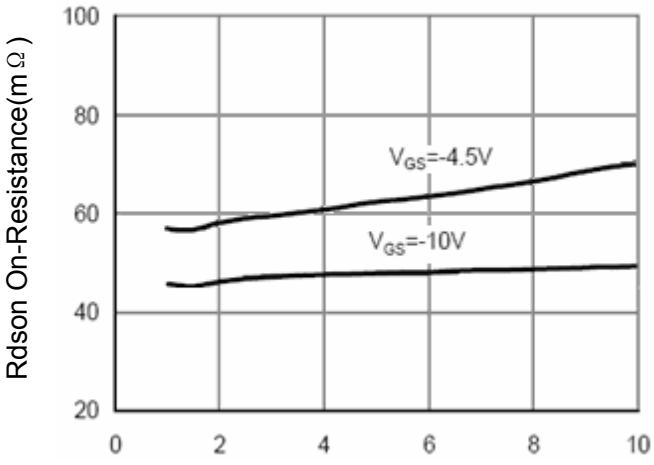


Figure 6 Drain-Source On-Resistance

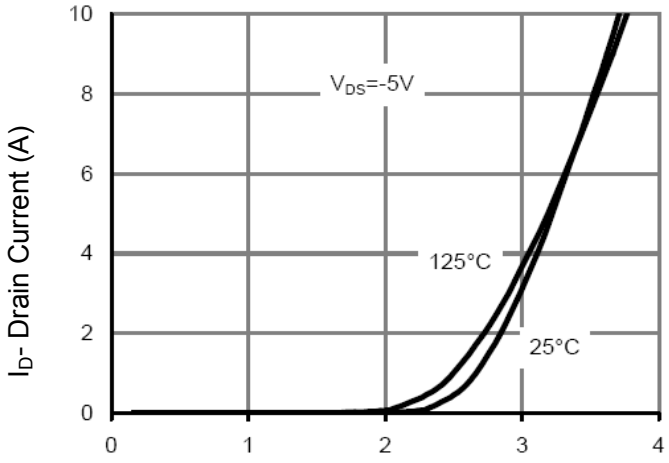


Figure 7 Transfer Characteristics

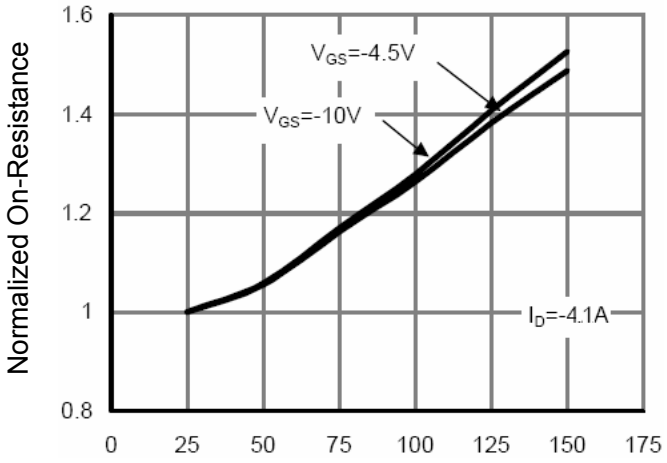


Figure 8 Drain-Source On-Resistance

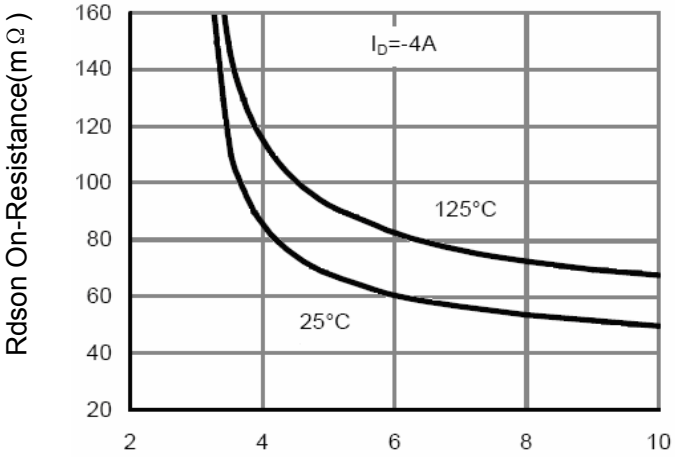


Figure 9 Rdson vs Vgs

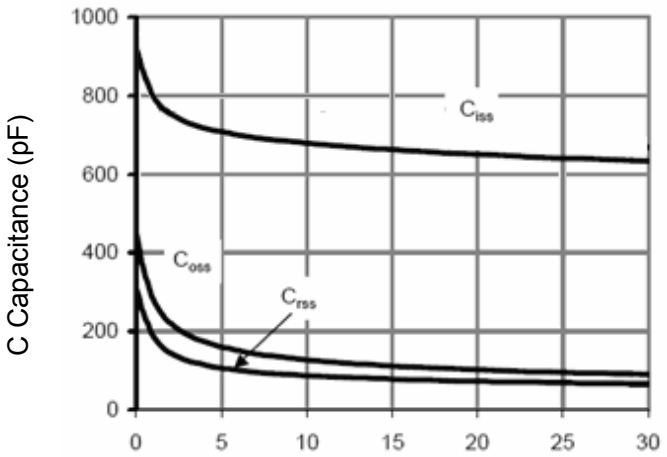


Figure 10 Capacitance vs Vds

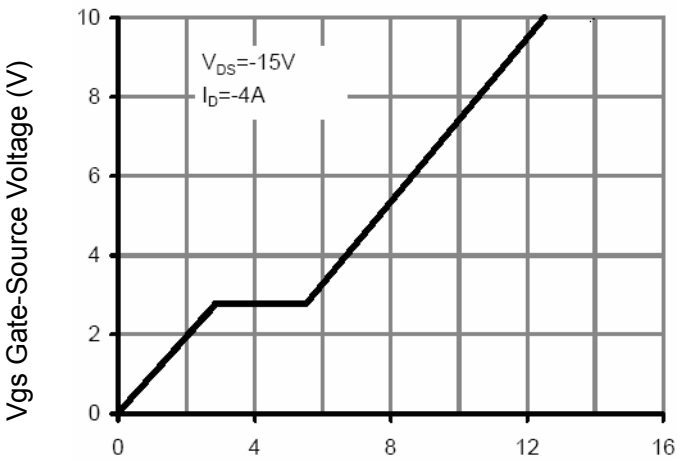


Figure 11 Gate Charge

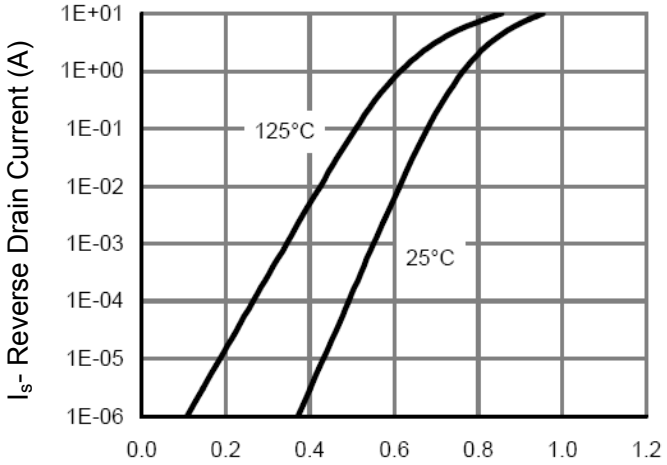


Figure 12 Source- Drain Diode Forward

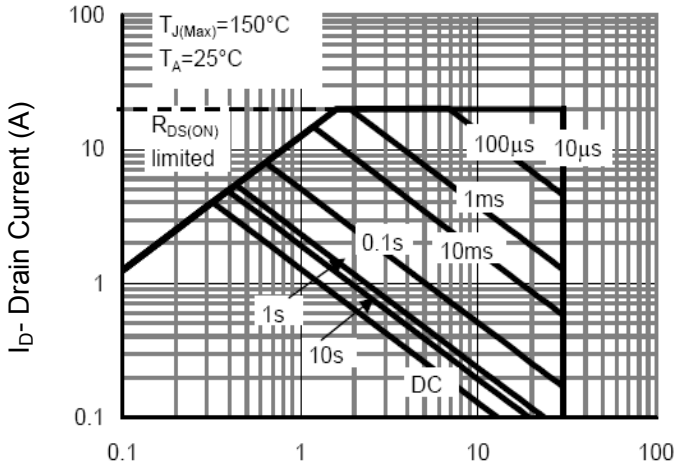


Figure 13 Safe Operation Area

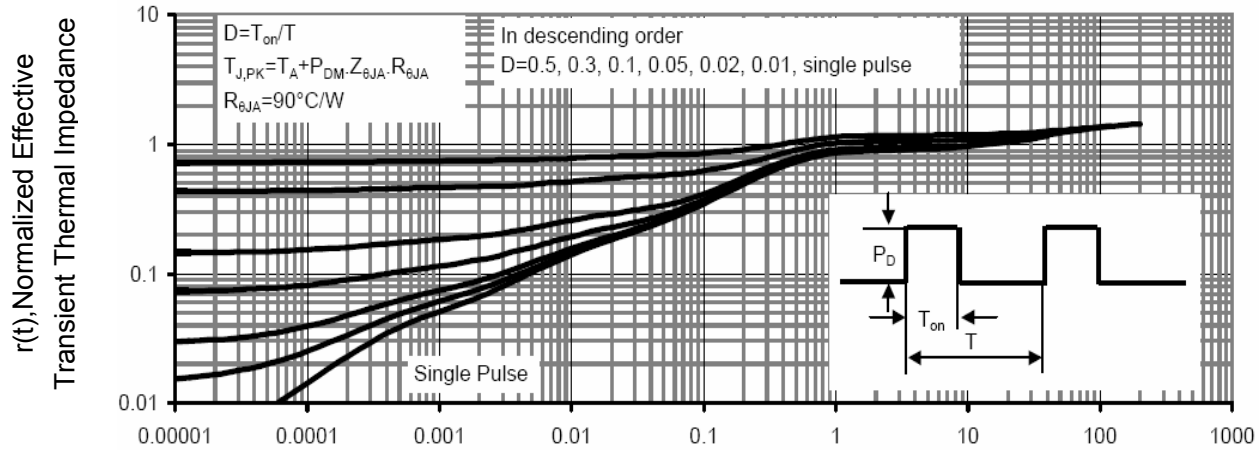
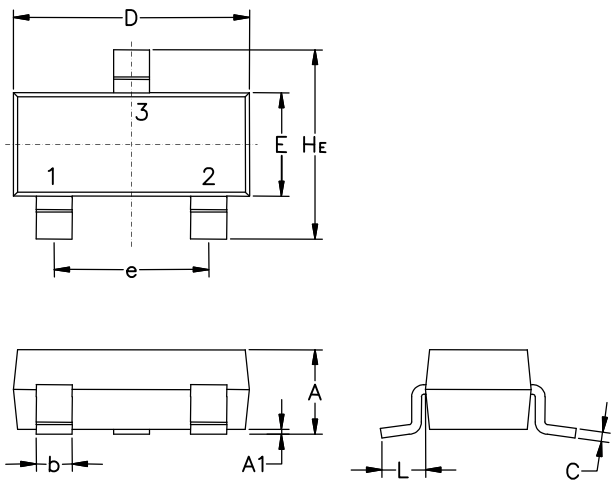


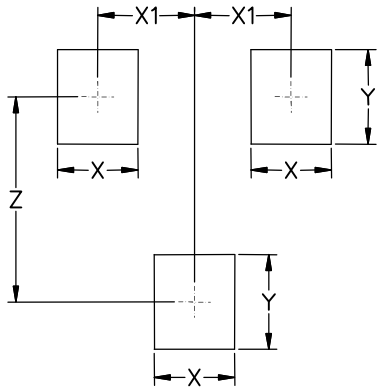
Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Outline & Dimensions



Symbol	Millimeters			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.15	0.18	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

Soldering Footprint



Symbol	Millimeters	Inches
X	0.80	0.031
X1	0.95	0.037
Y	0.90	0.035
Z	2.00	0.079

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